

1A 20V Low VF (1.00x1.00mm)

Chip Information

Chip Size	1.00 x 1.00mm
Pad Size	0.89 x 0.89mm
Chip Quantity	10928 pcs/wafer
Scribe Line Width	50um
Passivation	PSG
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	20	V	
Non-Repetitive Peak Reverse Voltage	VRSM	20	V	
Maximum DC Blocking Voltage	VR	20	V	
Average Forward Rectified Current	IF(AV)	1000	mA	
Peak Forward Surge Current	IFSM	10	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition	
Maximum Forward Voltage	VF1	0.360		0.340	V	IF=1000mA Ta=25degC	
	VF2				V		
	VF3				V		
	VF4				V		
	VF5				V		
Maximum DC Reverse Current	IR1	1000	300	95	uA	VR=20V Ta=25degC	
	IR2				uA		VR=20V Ta=100degC
	IR3				uA		
	IR4				uA		
Reverse Breakdown Voltage	BV	20	25	35	V	IR=500uA	
Junction Capacitance	Cj			54	pF	VR=10V f=1MHz	
Reverse Recovery Time	trr				nS		

Ordering Information

Chip Type	Chip Thickness	Back Metal
YCE715	180 +/- 20um	Au(For Eutectic)
YCE717	150 +/- 20um	Au(For Eutectic)
YCE716	180 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:
Designed For FS1J2E